# Very Low Forward Voltage **Trench-based Schottky Rectifier**

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC–DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

#### **Mechanical Characteristics**

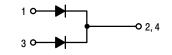
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

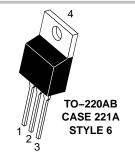


## **ON Semiconductor®**

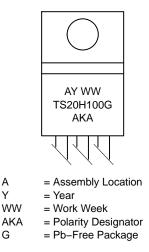
www.onsemi.com

#### **PIN CONNECTIONS**





### MARKING DIAGRAM



А

Y

G

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

#### MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 126^{\circ}C$ ) (Rated $V_R$ , $T_C = 136^{\circ}C$ )	Per device Per diode	I <sub>F(AV)</sub>	20 10	A
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 123°C) (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 134°C)	Per device Per diode	I <sub>FRM</sub>	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	125	A
Operating Junction Temperature		TJ	-55 to +150	°C
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Typical Thermal Resistance per Device (Note 1) Junction-to-Case	$\begin{array}{c} R_{\thetaJC} \\ R_{\thetaJA} \end{array}$	1.5	°C/W
Junction-to-Ambient		69.5	°C/W

1. Assumes 150 mm<sup>2</sup> 1 oz. copper bond pad, on a FR4 board.

#### ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

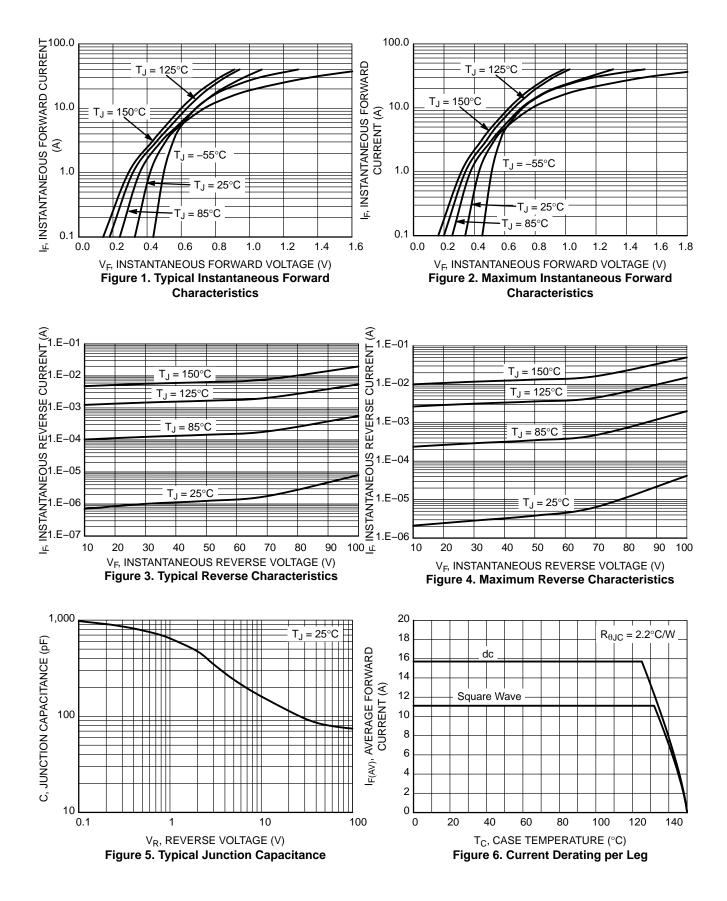
Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) $(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$ $(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$	۷F	0.58 0.74	_ 0.78	V
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$		0.53 0.63	_ 0.66	
Maximum Instantaneous Reverse Current (Note 2) $(V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C})$	I <sub>R</sub>	2 2		μA mA
(Rated dc Voltage, $T_J = 25^{\circ}C$ ) (Rated dc Voltage, $T_J = 125^{\circ}C$ )		8 5.5	42 15	μA mA
Diode Capacitance (Rated dc Voltage, T <sub>J</sub> = 25°C)	C <sub>d</sub>	75	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width =  $300 \,\mu$ s, Duty Cycle  $\leq 2.0\%$ 

#### **ORDERING INFORMATION**

Device	Package	Shipping
NRTSV20H100CTG	TO-220AB (Pb-Free)	50 Units / Rail

### **TYPICAL CHARACTERISTICS**



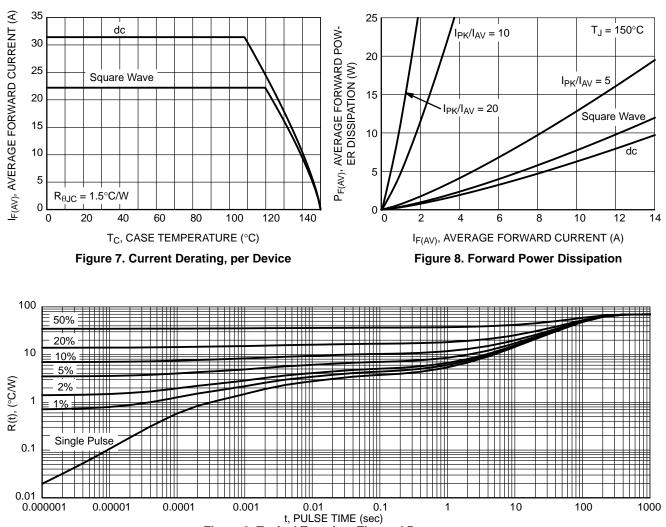
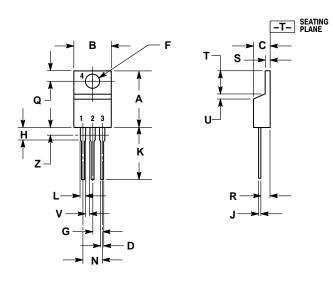


Figure 9. Typical Transient Thermal Response

#### PACKAGE DIMENSIONS

**TO-220** CASE 221A-09 ISSUE AH



	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Ζ		0.080		2.04

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

NOTES:

1.

2. 3.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all aws, regulations and safety requirements or standards, regardless of any support or applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights or the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application. Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative